

S/N 08/903,453

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al.

Examiner: V. Martin Wallace

Serial No.: 08/903,453

Group Art Unit: 2815

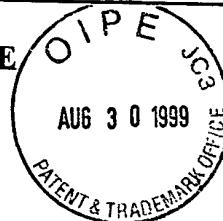
Filed: July 29, 1997

Docket: 303.378US1

Title: CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS

AMENDMENT AND RESPONSE

Assistant Commissioner for Patents  
Washington, D.C. 20231



In response to the Office Action mailed April 27, 1999, please amend the above-identified application as follows.

IN THE CLAIMS

Please amend the claims as follows:

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3.(Amended) An integrated circuit memory device supported by a semiconductor substrate, the device comprising:

a source and a drain separated by a channel supported by a semiconductor substrate;

a floating gate supported by the substrate and extending between the source and drain above the channel;

a control gate formed adjacent to and insulated from the floating gate; and  
an insulative layer of amorphous carburized silicon formed between the channel

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and the floating gate.

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4.(Amended) An integrated circuit capacitor supported by a semiconductor substrate, the capacitor comprising:

a first conductor layer supported by the substrate;

a dielectric layer of amorphous carburized silicon formed on top of the first conductor layer; and

a second conductor layer formed on top of the dielectric layer.

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